

RGTH00TS65

650V 50A Field Stop Trench IGBT

| V_{CES} | 650V |
|-----------------------------|------|
| I _{C(100°C)} | 50A |
| V _{CE(sat) (Typ.)} | 1.6V |
| P_D | 277W |

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

Applications

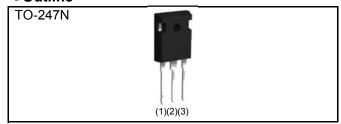
PFC

UPS

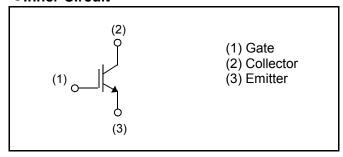
Power Conditioner

ΙH

Outline



●Inner Circuit



Packaging Specifications

| | Packaging | Tube |
|--------------------------------|-----------------|------------|
| | - | |
| Typo | Tape Width (mm) | - |
| Type Basic Ordering Unit (pcs) | | 450 |
| | Packing code | C11 |
| | Marking | RGTH00TS65 |

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

| Parameter | | Symbol | Value | Unit |
|--|------------------------|--------------------|-------------|------|
| Collector - Emitter Voltage | | V_{CES} | 650 | V |
| Gate - Emitter Voltage | | V_{GES} | ±30 | V |
| T _C = 25°C | | I _C | 85 | А |
| Collector Current | T _C = 100°C | I _C | 50 | А |
| Pulsed Collector Current | | I _{CP} *1 | 200 | А |
| $T_C = 25^{\circ}C$ | | P_{D} | 277 | W |
| Power Dissipation $T_C = 100^{\circ}C$ | | P_{D} | 138 | W |
| Operating Junction Temperature | | T _j | -40 to +175 | °C |
| Storage Temperature | | T _{stg} | -55 to +175 | °C |

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

| Parameter | Symbol | Values | | | Unit |
|---|-------------------|--------|------|------|------|
| raiametei | | Min. | Тур. | Max. | Uill |
| Thermal Resistance IGBT Junction - Case | $R_{\theta(j-c)}$ | - | - | 0.54 | °C/W |

ullet IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

| Parameter | Symbol | Conditions | Values | | | Unit |
|--|---------------------|--|--------|------|------|-------|
| r ai ai i i e te i | Symbol Conditions – | | Min. | Тур. | Max. | Offic |
| Collector - Emitter Breakdown Voltage | BV _{CES} | $I_{C} = 10 \mu A, V_{GE} = 0 V$ | 650 | ı | ı | V |
| Collector Cut - off Current | I _{CES} | V _{CE} = 650V, V _{GE} = 0V | 1 | 1 | 10 | μΑ |
| Gate - Emitter Leakage Current | I _{GES} | $V_{GE} = \pm 30V, V_{CE} = 0V$ | 1 | - | ±200 | nA |
| Gate - Emitter Threshold Voltage | $V_{GE(th)}$ | $V_{CE} = 5V, I_{C} = 34.7 \text{mA}$ | 4.5 | 5.5 | 6.5 | V |
| | | I _C = 50A, V _{GE} = 15V | | | | |
| Collector - Emitter Saturation Voltage | $V_{CE(sat)}$ | T _j = 25°C | - | 1.6 | 2.1 | V |
| | | T _j = 175°C | - | 2.1 | - | |

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

| Darameter | Symbol | Conditions | Values | | | Unit |
|----------------------------------|---------------------|---|--------|---------|------|-------|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Offic |
| Input Capacitance | C _{ies} | V _{CE} = 30V | - | 2740 | - | |
| Output Capacitance | C _{oes} | V _{GE} = 0V | - | 106 | - | pF |
| Reverse Transfer Capacitance | C _{res} | f = 1MHz | - | 43 | - | |
| Total Gate Charge | Q_g | V _{CE} = 300V | - | 94 | - | |
| Gate - Emitter Charge | Q_{ge} | I _C = 50A | - | 22 | - | nC |
| Gate - Collector Charge | Q_{gc} | V _{GE} = 15V | - | 31 | - | |
| Turn - on Delay Time | t _{d(on)} | I _C = 50A, V _{CC} = 400V | - | 39 | - | |
| Rise Time | t _r | $V_{GE} = 15V, R_G = 10\Omega$ | - | 63 | - | |
| Turn - off Delay Time | $t_{d(off)}$ | T _j = 25°C | - | 143 | - | ns |
| Fall Time | t _f | Inductive Load | - | 50 | - | |
| Turn - on Delay Time | t _{d(on)} | I _C = 50A, V _{CC} = 400V | - | 39 | - | |
| Rise Time | t _r | $V_{GE} = 15V, R_G = 10\Omega$ | - | 63 | - | 20 |
| Turn - off Delay Time | t _{d(off)} | T _j = 175°C | - | 159 | - | ns |
| Fall Time | t _f | Inductive Load | - | 62 | - | |
| | | I _C = 200A, V _{CC} = 520V | | | | |
| Reverse Bias Safe Operating Area | RBSOA | $V_P = 650V, V_{GE} = 15V$ | FU | LL SQUA | RE | - |
| | | $R_G = 60\Omega, T_j = 175^{\circ}C$ | | | | |

• Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

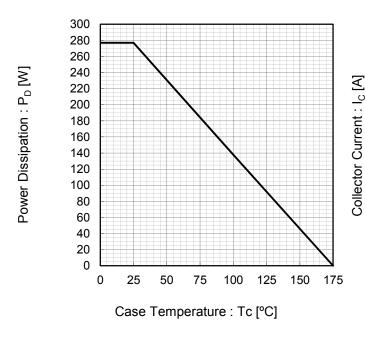
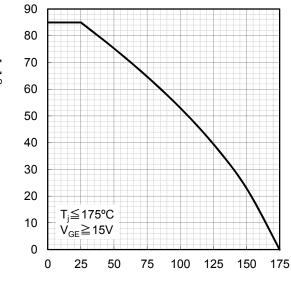


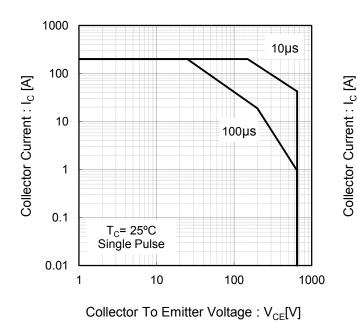
Fig.2 Collector Current vs. Case Temperature



Case Temperature : Tc [°C]

Fig.4 Reverse Bias Safe Operating Area

Fig.3 Forward Bias Safe Operating Area



220 200 180 160 140 120

240

100 80 60 40 T_i≦175°C 20 0 200 400 600 800

Collector To Emitter Voltage : $V_{CE}[V]$

Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

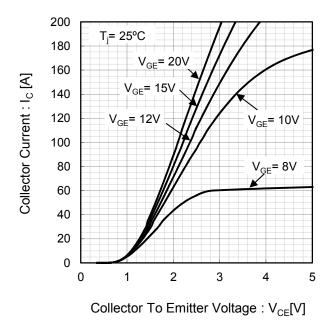
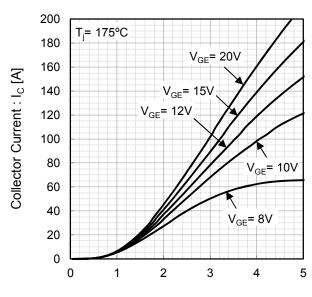


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V_{CE}[V]

Fig.7 Typical Transfer Characteristics

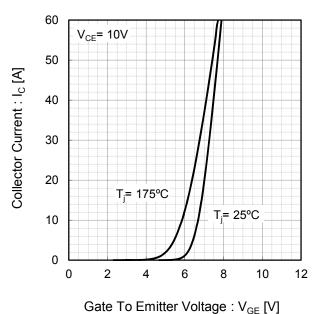
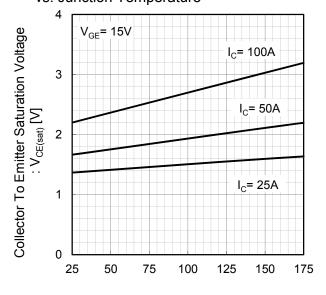


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

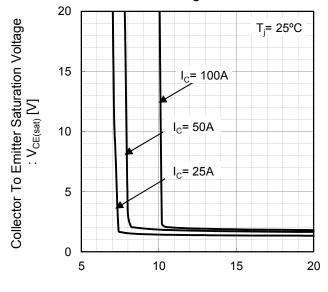
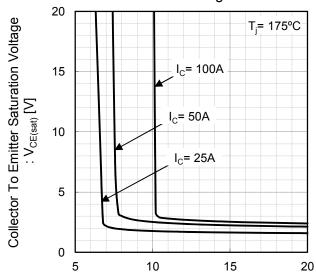


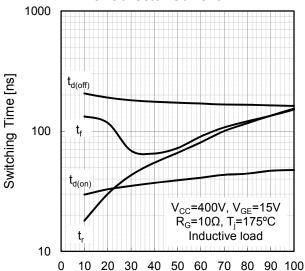
Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : $V_{GE}[V]$

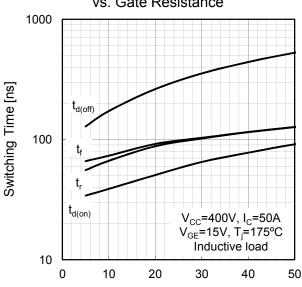
Gate To Emitter Voltage : V_{GE} [V]

Fig.11 Typical Switching Time vs. Collector Current



Collector Current : I_C [A]

Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance : $R_G[\Omega]$

• Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

10 E_{off} 0.1 E_{off} $V_{CC}=400V, V_{GE}=15V$ $E_{G}=10\Omega, T_{J}=175^{\circ}C$ Inductive load

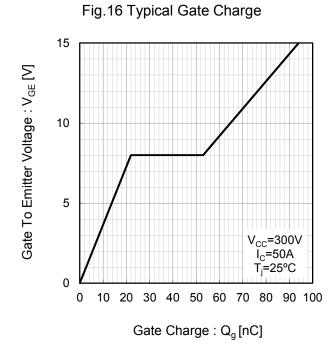
0 10 20 30 40 50 60 70 80 90 100

Collector Current : I_{C} [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] $\mathsf{E}_{\mathsf{off}}$ 1 0.1 V_{CC}=400V, I_C=50A V_{GE}=15V, T_j=175°C Inductive load 0.01 10 20 0 30 40 50 Gate Resistance : $R_G[\Omega]$

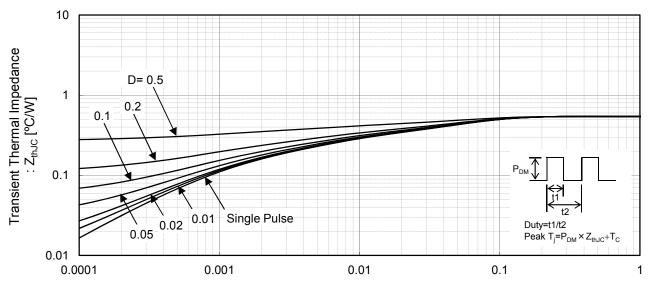
Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz $V_{GE}=0V$ T_i=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V_{CE}[V]



•Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

●Inductive Load Switching Circuit and Waveform

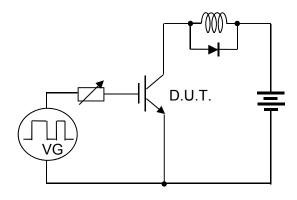


Fig.18 Inductive Load Circuit

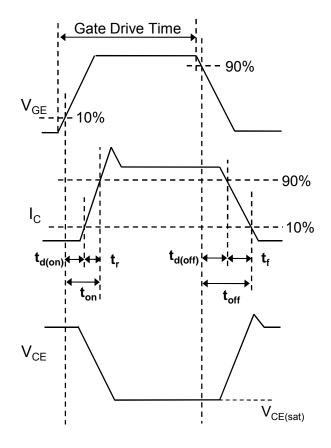


Fig.19 Inductive Load Waveform

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RGTH00TS65 - Web Page

Distribution Inventory

| Part Number | RGTH00TS65 |
|-----------------------------|------------|
| Package | TO-247N |
| Unit Quantity | 450 |
| Minimum Package Quantity | 450 |
| Packing Type | Bulk |
| Constitution Materials List | inquiry |
| RoHS | Yes |